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	Application No.	Applicant(s)
Nadio a R. Allowski 114.	10/609,476	FUJIOKA ET AL.
Notice of Allowability	Examin r	Art Unit
	Stephen W. Smoot	2813
The MAILING DATE of this communication appe All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this app or other appropriate communication GHTS. This application is subject to	plication. If not included will be mailed in due course. THIS
1. A This communication is responsive to applicant's amendment	nt filed on 17 November 2004.	
2. ☑ The allowed claim(s) is/are <u>1-35</u> .		•
3. $igotimes$ The drawings filed on <u>01 July 2003</u> are accepted by the Ex	aminer.	
 4. Acknowledgment is made of a claim for foreign priority una a) All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)). * Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 	been received. been received in Application No cuments have been received in this of this communication to file a reply	national stage application from the
5. A SUBSTITUTE OATH OR DECLARATION must be submit INFORMAL PATENT APPLICATION (PTO-152) which give		
 CORRECTED DRAWINGS (as "replacement sheets") mus (a) ☐ including changes required by the Notice of Draftspers 1) ☐ hereto or 2) ☐ to Paper No./Mail Date (b) ☐ including changes required by the attached Examiner's Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR 1. each sheet. Replacement sheet(s) should be labeled as such in the state of the sheet of the state of the sheet of the state of the sheet of t	on's Patent Drawing Review (PTO- s Amendment / Comment or in the C 84(c)) should be written on the drawin	Office action of age in the front (not the back) of
 DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT 		
 Attachment(s) 1. ☐ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☐ Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date 8-30-04 	6. ☐ Interview Summary Paper No./Mail Dat	ie
 4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material 	 8.	ent of Reasons for Allowance
	Stephen W Patent Exam	smoot iner /AU 2813

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DETAILED ACTION

This Office action is in response to applicant's amendment filed on 17 November 2004.

Allowable Subject Matter

- 1. Claims 1-35 are allowed.
- 2. The following is an examiner's statement of reasons for allowance:
 - Claims 1-11 are allowed because the prior art of record does not teach or suggest, in combination with the other claim limitations, a method for manufacturing a semiconductor device that includes forming a metal oxide film on a semiconductor substrate utilizing a dual stage deposition step with a first stage that includes introducing both a material gas and an oxidizing gas and a second stage for subsequently introducing a second oxidizing gas, wherein the flow rate of the oxidizing gas is less than the flow rate of the second oxidizing gas, and wherein the dual stage deposition step is repeated two or more times;
 - Claims 12-24 are allowed because the prior art of record does not teach or suggest, in combination with the other claim limitations, a method for

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manufacturing a semiconductor device that includes forming an insulating film corresponding to a capacitor formed on a semiconductor substrate utilizing a dual stage deposition step with a first stage that includes introducing both a material gas and an oxidizing gas and a second stage for subsequently introducing a second oxidizing gas, wherein the flow rate of the oxidizing gas is less than the flow rate of the second oxidizing gas, and wherein the dual stage deposition step is repeated two or more times; and

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Claims 25-35 are allowed because the prior art of record does not teach or suggest, in combination with the other claim limitations, a method for manufacturing a semiconductor device that includes forming a metal oxide film on a semiconductor substrate utilizing a dual stage deposition step with a first stage that includes introducing both a material gas and an oxidizing gas, wherein the material gas contains a metal that corresponds to the metal of the metal oxide, and a second stage for subsequently introducing a second oxidizing gas, wherein the flow rate of the oxidizing gas is less than the flow rate of the second oxidizing gas, and wherein the dual stage deposition step is repeated two or more times.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

3. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Stephen W. Smoot whose telephone number is 571-272-1698. The examiner can normally be reached on M-F (8:00 am to 4:30 pm).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl Whitehead, Jr. can be reached on 571-272-1702. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).